Notice of Allowability	Application No.	Applicant(s)
	10/810,419	ADAM ET AL.
	Examiner	Art Unit
	PHUC T. DANG	2818
The MAILING DATE of this communication apperall claims being allowable, PROSECUTION ON THE MERITS IS (herewith (or previously mailed), a Notice of Allowance (PTOL-85) NOTICE OF ALLOWABILITY IS NOT A GRANT OF PATENT RIG	(OR REMAINS) CLOSED in this apport of the communication GHTS. This application is subject to	plication. If not included will be mailed in due course. THIS
1. X This communication is responsive to amendment filed on A	<u>ugust 4, 2006</u> .	
2. X The allowed claim(s) is/are 1-5 and 7-17 (renumbered as in	new claims 1-16).	
<ul> <li>3.  Acknowledgment is made of a claim for foreign priority un</li> <li>a) All</li> <li>b) Some*</li> <li>c) None</li> <li>of the:</li> <li>1.  Certified copies of the priority documents have</li> </ul>		
<ol><li>Certified copies of the priority documents have</li></ol>	been received in Application No	·
<ol><li>Copies of the certified copies of the priority doc</li></ol>	cuments have been received in this	national stage application from the
International Bureau (PCT Rule 17.2(a)).		
* Certified copies not received:		
Applicant has THREE MONTHS FROM THE "MAILING DATE" of noted below. Failure to timely comply will result in ABANDONM THIS THREE-MONTH PERIOD IS NOT EXTENDABLE.		complying with the requirements
<ol> <li>A SUBSTITUTE OATH OR DECLARATION must be submi INFORMAL PATENT APPLICATION (PTO-152) which give</li> </ol>		
5. CORRECTED DRAWINGS ( as "replacement sheets") mus	t be submitted.	
(a)  including changes required by the Notice of Draftspers	on's Patent Drawing Review (PTO-	948) attached
1)  hereto or 2)  to Paper No./Mail Date		
(b) ☐ including changes required by the attached Examiner's Paper No./Mail Date	Amendment / Comment or in the C	Office action of
Identifying indicia such as the application number (see 37 CFR 1. each sheet. Replacement sheet(s) should be labeled as such in the		
<ol> <li>DEPOSIT OF and/or INFORMATION about the deposit attached Examiner's comment regarding REQUIREMENT I</li> </ol>		
Attachment(s)		
1. Notice of References Cited (PTO-892)	5. Notice of Informal F	Patent Application (PTO-152)
2. Notice of Draftperson's Patent Drawing Review (PTO-948)	6. Interview Summary	
3. Information Disclosure Statements (PTO-1449 or PTO/SB/0 Paper No./Mail Date	Paper No./Mail Da 8), 7. ⊠ Examiner's Amenda	ment/Comment
Examiner's Comment Regarding Requirement for Deposit of Biological Material	8. 🛛 Examiner's Stateme	ent of Reasons for Allowance
-	9.  Other	,
		PHUC T DANG Primary Examiner Art Unit: 2818

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## **DETAILED ACTION**

## Response to Amendment

1. This Office Action is in response to Amendment filed on August 4, 2006.

Claim 1 has been amended.

Claim 6 has been canceled.

Claims 1-5 and 7-25 are pending in the application.

## **Examiner's Amendment**

2. An Examiner's Amendment to the record appears below. Should the changes and/or additions be unacceptable to applicant, an amendment may be filed as provided by 37 C.F.R. 1.312. To ensure consideration of such an amendment, it MUST be submitted no later than the payment of the Issue Fee.

Authorization for this Examiner's Amendment was considered as follows:

3. In claim 1, line 3, "... a sem iconductor substrate ..." has been amended to -- a semiconductor substrate ... --.

In claim 10, line 13, " ... interconnect said first, second ... " has been amended to -- ... interconnect said first, second ... --.

4. Claims 18-25 have been canceled.

Claims 1-5 and 7-17 are pending in the present application at this time for examination.

Claims 1-5 and 7-17 are renumbered as in new claims 1-16.

## Examiner's Statement of Reasons for Allowance

5. Claims 1-5 and 7-17 are allowed.

The following is an examiner's statement of reasons for allowance:

With respect to claim 1, the prior art of record, taken alone or in combination, fails to teach or reasonably suggests a method for fabricating a tri-gate semiconductor device, comprising forming a low voltage core gate dielectric layer over the low voltage core region, including forming an intermediate core gate dielectric layer over an intermediate core region; wherein forming the low voltage core gate dielectric layer and the intermediate core gate dielectric layer is conducted in the presence of an environment containing nitrogen, in combination with the rest of the limitations of claim 1.

With respect to claim 10, the prior art of record, taken alone or in combination, fails to teach or reasonably suggests a method for manufacturing a tri-gate integrated circuit, comprising a step of forming interconnects extending through dielectric layers located over first, second, and third transistor gates to interconnect the first, second and third transistor gates to form an operative trigate integrated circuit, in combination with the rest of the limitations of claim 10.

- 7. Any comments considered necessary by applicant must be submitted no later than the payment of the issue fee and, to avoid processing delays, should preferably accompany the issue fee. Such submission should be clearly labeled "Comments on Statement of Reasons for Allowance".
- Any inquiry concerning this communication or earlier communications from the examiner should be directed to Phuc T. Dang whose telephone number is (571) 272-1776. The examiner can normally be reached on 8:00 am-5:00 pm.

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If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Harvey O Minsun can be reached on (571) 272-1835. The fax phone numbers for the organization

where this application or proceeding is assigned are 571-273-8300 for regular communications and After Final communications.

Any inquiry of a general nature or relating to the status of this application or proceeding 10. should be directed to the receptionist whose telephone number is 703-308-0956.

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Phuc T. Dang

Primary Examiner

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